# **Power MOSFET** -30V, 150mΩ, -2A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

#### **Features**

- Low On-Resistance
- 4V drive
- Pb-Free, Halogen Free and RoHS compliance

## **Typical Applications**

• Load Switch

#### **SPECIFICATIONS**

#### **ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±20	<b>V</b>
Drain Current (DC)	ID	-2	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-8	Α
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

  2 : This product is designed to "ESD immunity<200V\*", so please take care when
  - handling.
    - \*Machine Model

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit		
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	$R_{\theta JA}$	156.2	°C/W		

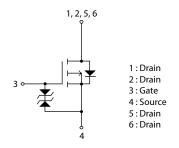


### ON Semiconductor®

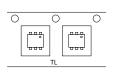
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max		
-30V	150mΩ@ –10V			
	255mΩ@ -4.5V	-2A		
	292mΩ@ –4V			

#### **ELECTRICAL CONNECTION** P-Channel



#### **PACKING TYPE: TL**



#### MARKING



#### **ORDERING INFORMATION**

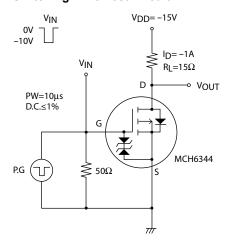
See detailed ordering and shipping information on page 5 of this data sheet.

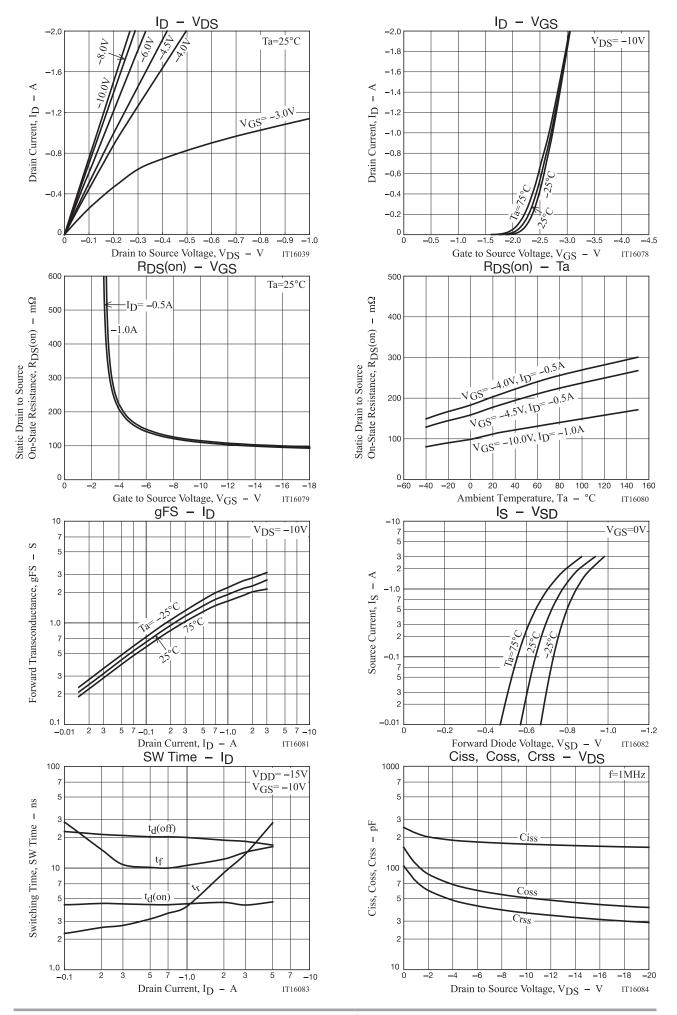
### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 3)

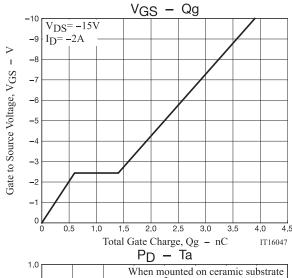
Parameter	Symbol	Conditions	Value			Unit	
Farameter	Parameter Symbol Conditions		min	typ	max	Offic	
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>G</sub> S=0V	-30			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ	
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Gate Threshold Voltage VGS(th)		V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V	
Forward Transconductance	gFS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1A		1.9		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-1A, V <sub>G</sub> S=-10V		115	150	mΩ	
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-4.5V		182	255	mΩ	
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-4V		208	292	mΩ	
Input Capacitance	Ciss	V <sub>DS</sub> =–10V, f=1MHz		172		pF	
Output Capacitance	Coss			51		pF	
Reverse Transfer Capacitance	Crss			36		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			4.5		ns	
Rise Time	tr	See specified Test Circuit		4.2		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)			20		ns	
Fall Time	tf			10.6		ns	
Total Gate Charge	Qg			3.9		nC	
Gate to Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A		0.6		nC	
Gate to Drain "Miller" Charge	Qgd			0.8		nC	
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =-2A, V <sub>GS</sub> =0V		-0.86	-1.5	V	

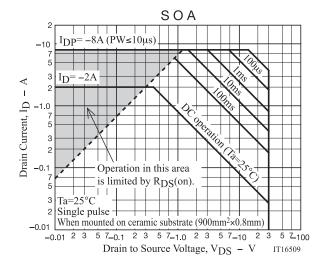
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

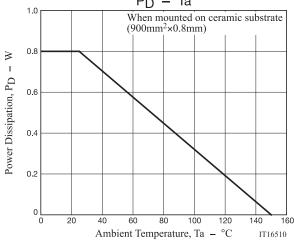
# **Switching Time Test Circuit**

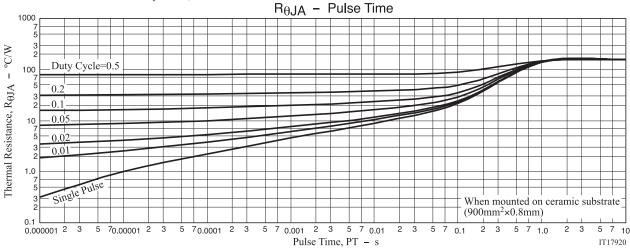








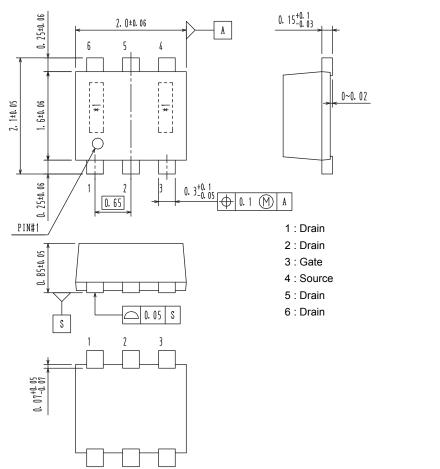




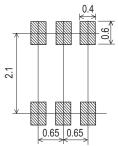
#### PACKAGE DIMENSIONS

unit : mm

SC-88FL / MCPH6 CASE 419AS ISSUE O



# Recommended Soldering Footprint



#### ORDERING INFORMATION

ONDERNING IN CIMILATION				
Device Marking		Package	Shipping (Qty / Packing)	
MCH6344-TL-H	YT	SC-88FL / MCPH6	2 000 / Tono 9 Dool	
MCH6344-TL-W			3,000 / Tape & Reel	

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6344 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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